## All<u>Proof-of-concept for an all-optical AND gate usingwith</u> photonic\_crystal quantum\_dot\_semiconductor optical amplifiers

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An Allall-optical AND gate using that uses photonic-crystal (PC) quantum-dot semiconductor optical amplifiers (QDSOA) is presented designed and simulated herein in this paper. We numerically analyze the The input—output characteristics of the gate are numerically analyzed by using rate equation model modeling to prove and show that the gate can operate at 160Gb/s. Moreover, in order to show the effectiveness of the proposed gate, we compare the The proposed gate is compared with the with conventional onedesign that uses an optical gate to evaluate its effectiveness in terms of with regard to degree of integration, energy signal output, device size, and power consumption and performance.

Introduction: Owing to progressing technology, Highhigh-speed and large\_capacity data transmission is required to cope with expanding increasing network traffic data[1].[1]. In current optical network, networks, an optical signal goestravels to its destination through optical fiber with beingfibers, and the signal is affected by noise, along the way. Thus, re-amplification, re-timing, and reshaping operations of the signal are essential for a reliable optical network. These days onic devices realize operation. Currently, electronic components are used to implement these operations and the problems are their; however, these nents have low processing speed limitation and consume high energy during optical-to-electrical signal conversion and vice versad for optic electric/electric optic conversion[2]. In order to cope with these problems, all optical signal [21]. Signal processing is required and many nt that uses all-optical components can avoid these limitations, and researchers worked on and developed are actively pursuing all-optical signal ing components. Quantum-dot semiconductor optical amplifiers (QDSOA) are optical devices which realize this technology, QDSOA is one of these es whichthat can be useful in many applications owing to its relatively fast gain recovery time and nonlinear optics because of it's fast gain recovery time and nonlinear optics effect[3]. QD'sThe confinement of electrons and electron holes in QDs enables fast gain recovery, and SOA's-gain saturation enables in the SOA leads to the nonlinear optics effect, respectively. On the other handln contrast, the photonic-crystal (PC) is a dielectric material which periodic pattern of two different refractive indexes; therefore, periodically. The lightwaves in specific light waves of a single bandwidth cannot propagate through the PC. PC waveguides (PCWs) useexploit this characteristic which can be obtained with a line-shaped recession in a PC slab with creating a line defect. They can confine the lightwayes. This linear recession confines the light wayes in the directions perpendicular and parallel to the direction of lightwayes. propagation. Moreover, theirthe dispersion relation between the PC refractive indices can slow down-decelerate lightwaves the wave velocity, which can be useful when in cases wherein they area PCW is combined with an SOA or ODSOA.

Similar to electronic logic gates, all-optical logic gates (AOLGs are the applications of all-optical devices which can operate) can manipulate binary inputs. Although many AOLGs using various all-optical devices have been developed using a variety of optical materials, the length of these gates is AOLGs tends to be larger than one-that of electrical logic gates because since all-optical devices require certain length components must be long enough to operate as a componentaccommodate the reflections of AOLGs the signal. For instance, a length of typical QDSOA is about approximately 2mm2-mm long [4], whereas the one of transistors, equivalent transistor used forin commercially available electronic devices; is about approximately 14nm]4-ml long [5]. Few researches discuss aboutstudies have focused on the length of device which the components in optical logic gates, although this is an important factor for concerning the developing development of devices with high-density integrated integrated integration and lessminimal energy consumption device. Thus, a we Therefore, propose PC-QDSOA assisted an all-optical AND gate; that uses PC-QDSOA components is proposed herein. AND gate playsgates play an important role for multiplexer and demultiplexer circuits whose applications are that are commonly used in communication systemsystems, computer memory and arithmetic logic unit. Inorder to show units. To demonstrate the effectiveness of the proposed gate, we numerically analyze the analyzed its input—output characteristics of the gate by using rate-equation equation modelmodels. To our knowledge, there is no research has been conducted about on the numerically analyzing numerical analysis of a PC-QDSOA assisted all-optical AND gate yet. TheOur results in this paper show indicate that the realization of the an all-optical AND gate is feasible with the proposed PC-QDSOA assisted all-optical AND gate waveguide could feasibly operate at 160Gb160 Gb/s and the proposed gate can achieve 9dBa maximum of 9-dB extinction ratio (ER

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**Comment** [Editor2]: Remark: Please verify if the edit retains your intended meaning.

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Comment [Editor4]: Remark: Note that this sentence has been edited to explain why alloptical components should be long enough. Please verify if the edit retains your intended meaning and clarify further if required.

## Comment [Editor5]:

## Tip: Serial comma

In American English, a comma (called serial or oxford comma) is inserted before "and" in a series.

with either zero group\_velocity dispersion and zero third\_order dispersions in a part a specific bandwidth. The waveguide can be achieved is fabricated by creating a line defeet line-shaped recession in a PC slab PC, which can be obtained, and the slab is fabricated by creating periodic round vacancy periodically vacancies on n-eladding and p-eladdingclad regions [7].

The operation of the PC-QDSOAs can be <u>studied</u> theoretically <u>studied by means of a using the rate-equation quation</u> model[8]. InAs QDs <u>consists of comprise</u> a ground state (GS), an excited state (ES), and an upper state (US). <u>A quantum wellQuantum wellS</u>

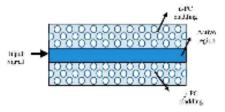


Fig. 1. Schematic diagram of the PC-QDSOA waveguide

(QW) is QWs) are the common carrier reservoirs for in QDs. Due to variability in the size and shape of QDs QDs exhibit different sizes and shapes with use of when using the Stranski-Krastanov mode, the therefore, carrier dynamics in the QDs can be described by using 1088 variables. Thus, athe rate equation of the PC-QDSOA is as follows:

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**Comment [Editor8]:** Remark: Please clarify your intended meaning herein.

$$\begin{split} \frac{\partial f_{n}^{(p)}}{\partial t} &= \frac{m_{n} f}{\partial N_{n}^{(p)}} - \frac{\sqrt{f_{n}^{(p)}}}{\sqrt{f_{n}^{(p)}}} = \frac{E_{n}^{(p)}}{E_{n}^{(p)}} \sum_{i=1}^{n} G_{i}^{(p)} \\ &= \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) - 10 \\ &= \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) - \frac{F_{n}^{(p)}}{E_{n}^{(p)}} \\ &= \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) \\ &= \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) \\ &+ \frac{F_{n}^{(p)}}{H_{n}^{(p)}} \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) \\ &- \frac{\sqrt{f_{n}^{(p)}}}{f_{n}^{(p)}} \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) \\ &- \frac{1}{N_{n}^{(p)}} \sum_{f_{n}^{(p)}} \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) \\ &- \frac{1}{N_{n}^{(p)}} \sum_{f_{n}^{(p)}} \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) \\ &- \frac{1}{N_{n}^{(p)}} \sum_{f_{n}^{(p)}} \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) \\ &- \frac{1}{N_{n}^{(p)}} \sum_{f_{n}^{(p)}} \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) \\ &- \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) \\ &- \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) \\ &- \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) \\ &- \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right) - \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(1 - f_{n}^{(p)}\right)\right) \\ &- \frac{f_{n}^{(p)}}{f_{n}^{(p)}} \left(\frac{f_{n}^{(p)}}{f_{n}^{(p)}$$

The term fWj'v) represents the carrier occupancy of the QW. Likewise,

 $\underline{fc(v)u:j}$ ,  $\underline{fc(v)e:j}$ , and  $\underline{fc(v)g:j}$ ,  $\underline{fu'jj''}$   $\underline{fe}$ , represents the carrier occupancy of the jth group of US, ES, and GS<sub>k</sub> respectively. The term  $r_k$  is the optical confinement factor at wavelength  $X_k$ . The termterms  $P_{k:m}$  and  $P_p$  represents represent the power

Comment [Editor9]: Remark: Please insert a comma after Equations (1), (2), and (3) and a period after Equation (4).

of the fethath photon mode and probe signal, respectively. The term a(X) represents the loss coefficient at athe wavelength  $X_{\perp}$  which ean beight the sum of the scattering and absorption losses. The term  $g_{mo}d(t, X_{k})$  is the effect on linear modal gain affected caused by slow light, and it can be expressed as the product of the slowdown factor, optical confinement enfinement factor, and linear material gain of the active region. The term  $g^{g} \wedge$  is the linear optical gain that the GS (ES) of the j-th QD group gives provides to the fel-th ES photon mode is given. More details about the PC-QDSOA structure can be found are provided in reference [8].

AND gate model: The Fig. 2 schematizes ie diagram of the PC-QDSOA assisted all-optical AND gate is shown in Fig.2. The AND operation principle is as follows: a modulated-data signal A (at wavelength  $X^{\circ}$ ) and a clock signal (at wavelength  $X_{c}$ ) are injected into the input to PC-QDSOA1. Then the signal Signal A will induce lesslow gain amplification on athe clock signal via cross-gain modulation (XGM) in the PC-QDSOA1 and; therefore, the logic outcomeoutput is always NOT A. In the same way as Repeating this operation, athe modulated-data signal NOT A (at wavelength  $X_{c}$ ) and a modulated-data signal B (at wavelength  $X_{s}$ , which can be the same as equal to the wavelength of data signal A) are injected into the

input to PC-QDSOA2, and the logic outcomeoutput is then A AND B.

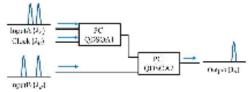


Fig. 2. Schematic diagram of the PC-QDSOA assisted all-optical AND gate

Results: We numerically analyze the The operation of the proposed gate withdesign is numerically analyzed using MATLAB 2016b and Optisystem 14.0.0. The physical parameters used for solving the rate equation ean be foundare provided in reference [8]. Table: 1 shows lists the fixed parameters used for following the numerical analysis: in this paper. The pulses are were Gaussian-shaped-pulses.

Table 1: The fixed parameters used for following in numerical analysis

Parameter	Value	Unit
Maximum power of Input A	10	mW
Maximum power of Input B	1	/W
Maximum power of Clock	100	/W
Wavelength of Input A	1307	nm
Wavelength of Input B	1307	nm
Wavelength of Clock	1310	nm
Full width at half maximum of pulse	1.2	
Transmission speed	160	Gb/s

To evaluate the proposed gate, we use the eye diagram, ER, and Q-factor arc used as appropriate metrics. The ER extinction ratio can be represented as ER[dB] = o logio (Pmin/Pmax), pmin\_represents minimum powerpower

of the binary signal ""1"." and an represents the maximum power of the "0" signal "0". The Q-factor can be represented as  $Q = (S_1 - S_0)/(a_1 + a_0)$ , [9] where  $S_r$  and  $S_0$  are the average powerpowers of signals ""1" and ""0"" and  $a_1$  and "0" a are the standard deviations of those signals.

Fig. 3 shows the analysis\_imulation results offer the input—output characteristics when with 6-mA current injection is 6mA. Fig. 4 shows an eye diagram of the output signal. The ER and Q-factor offer the output signal are 8.58 dB and 7.41, respectively. From these These results—it is said show that the proposed gate design can operate as an AND gate at 160 Gb/s [10]. On the other hand, because Since the gain recovery time varies due towith the level of current injection, we have also investigated the effect on power of varying current injection to on the power output from the proposed AND gate. Fig. Figs. 5 and Fig. 6, respectively, show the ERs and Q-factors\_of the output signals underwith different current injection, respectively-injected currents. The ERs and Q-factors are improving improve with increasing current injection because pattern—effect is decreasing, effects decrease. When current injection is over 9mA, there is few exceeds 9 mA, the ERs change slightly in ERs-because the maximum gain—recovery recovery

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Comment [Editor11]: Remark: Please explain more in this sentence about how these ER and Q-factor results are related to the device functioning as an AND gate.

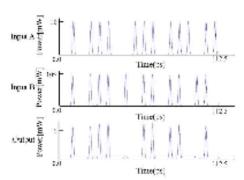


Fig. 3 Input—output characteristics offor PC-QDSOA all-optical assisted AND gate operation when current injection is 6m.46 m.4

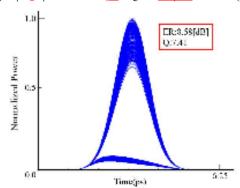


Fig. 4. Eye diagram of the output signal when with 6-mA current injection

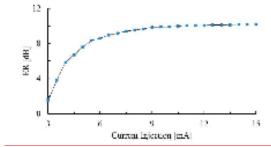


Fig. 5. ERs with varying current injection-is 6mA

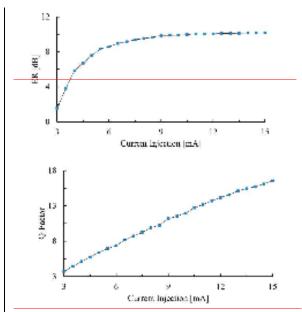


Fig. 5. ERs under different6. Q-factor with varying current injection

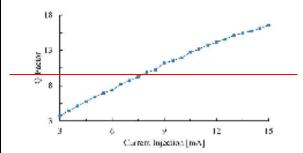


Fig. 6. Q-factor under different current injection

In order to show

To quantify the effectiveness of the proposed gate, we compare the proposed AND gate is compared with the oneg QDSOA\_assisted, whose gate without PC components. This design follows the same schematic diagram is same as the proposed one. The physicaldesign. Physical parameters and numerical analysis method of the methods used to analyze this QDSOA can be founded sign are provided in reference [4]. Fig.Figs. 7 and fig.8 show the comparison of current injection required to obtain each, respectively, plot ERs and Q-factors vs. current injection for QDSOA\_assisted AND gate and the proposed one, respectively. From fig.7, it is said that todesign. To obtain ER of about approximately 7.5dB.7.5 dB, the QDSOA\_assisted AND gate requires 3000mA3000 mA, whereas the proposed AND gatedesign requires only 5mA.5-mA injected current, Likewise, from fig.Fig. 8; shows that to obtain a Q-factor of about approximately 5, the QDSOA\_assisted AND gate requires 2800mA2800 mA injected current, whereas the proposed AND gatedesign requires only 4mA4 mA. Moreover, the device length of the QDSOA is 2mm2-mm long, whereas the one of the proposed PC-QDSOA is 1254m. From these results, less Jun This comparison demonstrates that the AND gate reduces energy consumption and lessdevice volume AND gate can be obtained with use of the proposed gatecompared with all-optical AND gates reported in the literature.

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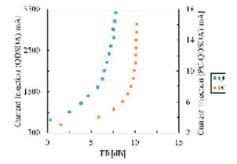


Fig. 7. ERs under different current injection

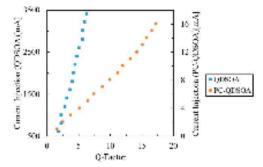


Fig. 8. Q-factor under different current injection

Conclusion: We have proposed designed a PC-QDSOA assisted-all-optical AND gate operating that can operate at 160Gb160 Gb/s and evaluated the performance. The measures of the proposed gate by using eye diagram, ER, and Q-factor. The results quantify the design's performance. Numerical analyses show that the proposed gate can operate as an AND gate at 160Gb160 Gb/s when current injection is over 6mA and better 6 mA. This performance can be achieved with improved by increasing current injection-because, as this would decrease pattern-effect decreases effects.

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## References

1 D. Bimberg, M. Laemmlin, C. Meuer, G. Fiol, M. Kuntz, A. Schliwa, N. N. Ledentsov and A. R. Kovsh, "Quantum Dot Amplifiers for 100 Gbit Ethernet, "ICTON, pp. 1924–1930, Jun. 2006.

2 B. Sartorius, "3R regeneration for all-optical networks, "7 ICTON, pp. 333-337, Aug. 2002.

Comment [Editor13]: Remark: Note that the terms "PC-QDSOA-assisted AND gate" and "PC-QDSOA all-optical AND gate" were interchangeably used. We have therefore used "PC-QDSOA all-optical AND gate" throughout the document for consistency.

Comment [Editor14]: Remark: Please provide page numbers for the reference wherever applicable.

3 I. Kang, C. Dorrer, L. Zhang, M. Dinu, M. Rasras, L. L. Buhl, S. Cabot, A. Bhardwaj, X. Liu, M. A. Cappuzzo, L. Gomez, A. Wong-Foy, Y. F. Chen, N. K. Dutta, S. S. Patel, D. T. Neilson, C.R. Giles, A. Piccirilli

and J. Jaques, "Characterization of the dynamical processes in all-optical signal processing using semiconductor optical amplifiers, "IEEE J. Sel. Topics Quantum Electron., vol. 14, no.3, pp. 758–769, May/Jun. 2008.

4 K. Abedi and H. Taleb, "Phase Recovery Acceleration in Quantum-Dot Semiconductor Optical Amplifiers, "J. Lightw. Technol., vol. 32, no.12, pp. 237—241, Jun. 2012.

5 (2017, Dec. 8), Intel Core i7-5557U specifications [Online]. Available: http://www.cpu-world.com/CPUs/Core\_i7/Intel-Core%20i7-Available: http://www.cpu-world.com/CPUs/Core\_i7/Intel-Core%20i7-5557U%20Mobile%20processor.html

6 M. Sugawara, H. Ebe, N. Hatori, M. Ishida, Y. Arakawa, T. Akiyama, K. Otsubo and Y. Nakata, "Theory of optical signal amplification and processing by quantum-dot semiconductor optical amplifiers, "

PhysRevB, vol. 69, Issno. 23, Jun. 2004.

7 O. Khayam and H. Benisty, "General recipe for Hatbands in photonic crystal waveguides, "Opt. Exp., vol. 17, no. 17, pp. 14634—14648, Aug.

8 H. Taleb and K. Abedi, "Optical Gaingain, Phasephase, and Refractive Index index Dynamics in Photonic Photonic Crystal crystal Quantum Quantum Dot dot Semiconductor Semiconductor Optical Optical Amplifiers amplifiers, "IEEE J. Quantum Electron., vol. 50, no. 8, pp. 605—612, Aug. 2014.

9 P. Agrawal, "Fiber-Optic Communication Systems, third ed., "Wiley, John & Sons., May. 2002.

10 D. Gayen, A. Bhattachryya, T. Chattopadhyay and J. Roy, "Ultrafast All-Optical Half Adder Using Quantum-Dot Semiconductor Optical Amplifier-Based Mach-Zehnder Interferometer," J. Lightw. Technol.,

vol. 30, <u>Issno</u>. 21, pp. 3387—3393, Sep. 2012.